Erratum: “Kinase detection with gallium nitride based high electron mobility transistors” [Appl. Phys. Lett. 103, 013701 (2013)]

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New versions of Figures 1(a), 3(a), 3(b), and 4(a) are provided. In Figure 1(a), the circles are now appropriately filled; the words “Source,” “Gate,” and “Drain” are now positioned appropriately, and the line border around the word “Drain” is the appropriate thickness. In Figures 3(a), 3(b), and 4(a), the lines near the top of each plot that indicate statistical significance are arranged appropriately.¹

FIG. 1.

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FIG. 3.

FIG. 4.

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